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| [Home](https://xitanghkust.github.io/index.htm)  People  [Projects](https://xitanghkust.github.io/projects.htm)  [Publications](https://xitanghkust.github.io/publications.htm)  [Teaching](https://xitanghkust.github.io/teaching.htm)  [Contact](https://xitanghkust.github.io/contact.htm) | |  |  | | --- | --- | |  | Patents | |  | [1] Jiannong Wang, **Xi Tang,** Baikui Li; Metal-Heterostructure-Metal (MHM) Ultraviolet Photodetectors, *US provisional.*  [2] Baikui Li, **Xi Tang**; Oto-electronic memory devices based on AlGaN/GaN heterostructures, (Chinese Patent App No. PCT/CN2018/082582)  [3] Kevin J. Chen, Baikui Li, **Xi Tang**; P-Doping-Free Schottky-on-Heterojunction Light-Emitting Diode and High-Electron-Mobility Light-Emitting Transistor (Publication Number: WO 2015/131846 A1)  [4] Kevin J. 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